

LOW DROP POWER SCHOTTKY RECTIFIER

MAJOR PRODUCTS CHARACTERISTICS

$I_{F(AV)}$	2 x 10 A
V_{RRM}	40 V
$T_j(\text{max})$	150°C
$V_F(\text{max})$	0.5 V

FEATURES AND BENEFITS

- LOW FORWARD VOLTAGE DROP MEANING VERY SMALL CONDUCTION LOSSES
- LOW DYNAMIC LOSSES AS A RESULT OF THE SCHOTTKY BARRIER
- INSULATED PACKAGE: ISOWATT220AB, TO-220FPAB
Insulating voltage = 200V DC
Capacitance = 12pF
- AVALANCHE CAPABILITY SPECIFIED

DESCRIPTION

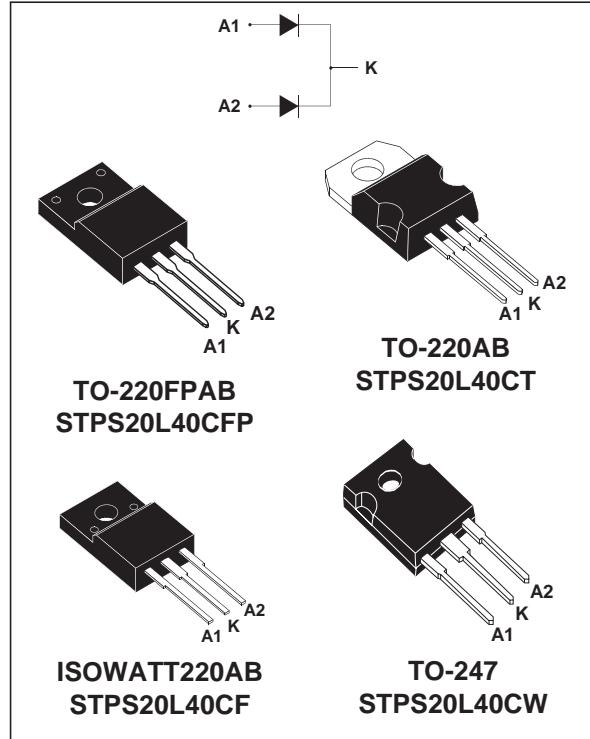
Dual center tap Schottky rectifiers designed for high frequency switched mode power supplies and DC to DC converters.

These devices are intended for use in low voltage, high frequency inverters, free-wheeling and polarity protection applications.

ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter				Value	Unit
V_{RRM}	Repetitive peak reverse voltage				40	V
$I_{F(\text{RMS})}$	RMS forward current				30	A
$I_{F(AV)}$	Average forward current	TO-220AB	$T_c = 135^\circ\text{C}$	Per diode	10	A
		TO-247	$\delta = 0.5$	Per device	20	
I_{FSM}	Surge non repetitive forward current	ISOWATT220AB	$T_c = 115^\circ\text{C}$	Per diode	10	A
		TO-220FPAB	$\delta = 0.5$	Per device	20	
I_{RRM}	Peak repetitive reverse current	tp = 10 ms Sinusoidal			180	A
I_{RSR}	Non repetitive peak reverse current	tp = 2 μs square F=1kHz			1	A
P_{ARM}	Repetitive peak avalanche power	tp = 1 μs $T_j = 25^\circ\text{C}$			4000	W
T_{stg}	Storage temperature range				- 65 to + 150	°C
T_j	Maximum operating junction temperature *				150	°C
dV/dt	Critical rate of rise of reverse voltage				10000	V/ μs

* : $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th}(j - a)}$ thermal runaway condition for a diode on its own heatsink



STPS20L40CF/CW/CT/CFP

THERMAL RESISTANCES

Symbol	Parameter			Value	Unit
R _{th(j-c)}	Junction to case	ISOWATT220AB TO-220FPAB	Per diode Total Coupling	4.5 3.5 2.5	°C/W
R _{th(j-c)}	Junction to case	TO-247	Per diode Total Coupling	2.2 1.20 0.3	°C/W
R _{th(j-c)}	Junction to case	TO-220AB	Per diode Total Coupling	2.2 1.3 0.3	°C/W

When the diodes 1 and 2 are used simultaneously :

$$\Delta T_j(\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$$

STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
I _R *	Reverse leakage current	T _j = 25°C	V _R = V _{RRM}			0.7	mA
		T _j = 100°C			15	35	mA
V _F *	Forward voltage drop	T _j = 25°C	I _F = 10 A			0.55	V
		T _j = 125°C	I _F = 10 A		0.44	0.5	
		T _j = 25°C	I _F = 20 A			0.73	
		T _j = 125°C	I _F = 20 A		0.62	0.72	

Pulse test : * tp = 380 μs, δ < 2%

To evaluate the conduction losses use the following equation :

$$P = 0.28 \times I_{F(AV)} + 0.022 I_{F}^2 (\text{RMS})$$

Fig. 1: Average forward power dissipation versus average forward current (per diode).

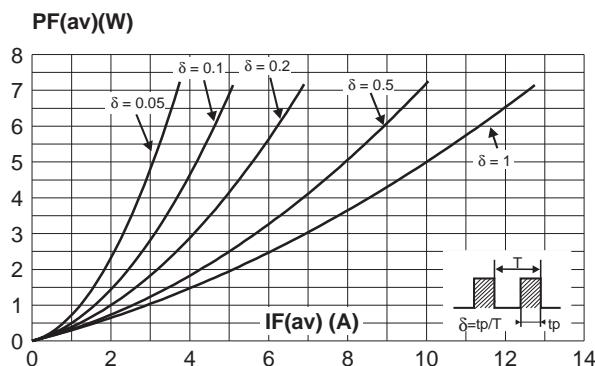
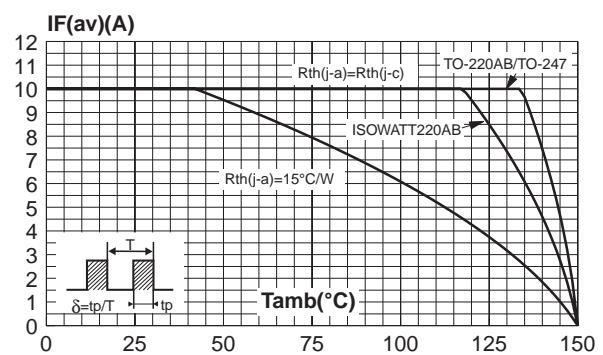


Fig. 2: Average forward current versus ambient temperature ($\delta = 0.5$, per diode).



STPS20L40CF/CW/CT/CFP

PACKAGE MECHANICAL DATA TO-247

REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.85		5.15	0.191	0.203	
D	2.20		2.60	0.086	0.102	
E	0.40		0.80	0.015	0.031	
F	1.00		1.40	0.039	0.055	
F1		3.00			0.118	
F2		2.00			0.078	
F3	2.00		2.40	0.078	0.094	
F4	3.00		3.40	0.118	0.133	
G		10.90			0.429	
H	15.45		15.75	0.608	0.620	
L	19.85		20.15	0.781	0.793	
L1	3.70		4.30	0.145	0.169	
L2		18.50			0.728	
L3	14.20		14.80	0.559	0.582	
L4		34.60			1.362	
L5		5.50			0.216	
M	2.00		3.00	0.078	0.118	
V		5°			5°	
V2		60°			60°	
Dia.	3.55		3.65	0.139	0.143	

- Cooling method : C
- Recommended torque value : 0.8m.N
- Maximum torque value : 1.0m.N

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS20L40CF	STPS20L40CF	ISOWATT220AB	2.1g	50	Tube
STPS20L40CFP	STPS20L40CFP	TO-220FPAB	2g	50	Tube
STPS20L40CT	STPS20L40CT	TO-220AB	2g	50	Tube
STPS20L40CW	STPS20L40CW	TO-247	4.4g	30	Tube

- Epoxy meets UL94,V0